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Substitute Form 1449		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	10/026,802
		Filing Date	December 27, 2001
		First Named Inventor	Hisashi Ohtani et al.
		Group Art Unit	2811
		Examiner Name	W. Mintel
Sheet 1 of 1	Attorney Docket Number	0756-2415	

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
mm		JP	63-318162		12/27/1988			Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
mm		Ultra LSI Process Data Handbook, April 15, 1982, pp. 124-125	Concise Stmt. MAY 12 2003

Examiner Signature	Date Considered	Jan 7, 2003
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<b>Form PTO-1449</b> (Rev. 8-83)	<b>U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>	<b>Docket No:</b> 740756-2415	<b>Serial No.</b> Not Yet Assigned
<b>INFORMATION DISCLOSURE STATEMENT</b>			
(Use several sheets if necessary)			

Applicant: Hisashi OHTANI et al.

Filing Date: December 27, 2001

Group: 2811

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		Filing Date: December 27, 2001	Group: 2811			
<b>U.S. PATENT DOCUMENTS</b>						
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